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ı	INFO	RMATION	DISC	LOSURE	Application Number	Based on 10/214,691	,
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ł	SIAI				First Named Inventor	Shunpei YAMAZAKI, et al.	
I		(use as many sheets	as necess	ary)	Group Art Unit	2826	
l					Examiner Name	Fetsum Abraham	
	Sheet	1	of	12	Attorney Docket Number	0756-7218	

			U.S. PATENT DOCUMEN	TS		
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. 2 See attached Kinds of U.S. Patent Documents. 2 Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 5 Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. Applicant is to place a check mark here if English language Translation is attached.

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Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number. Complete if Known Substitute for form 1449A/PTO Application Number Based on 10/214,691 INFORMATION DISCLOSURE August 9, 2002 Filing Oate STATEMENT BY APPLICANT Shunpei YAMAZAKI, et al. First Named laventor (use as many sheets as necessary) 2826 Group Art Unit Examiner Name Fetsum Abraham

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INFO	RMATION I	DISC	LOSURE	Application Number	Based on 10/214,691
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SIA				First Named Inventor	Shunpei YAMAZAKI, et al.
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				Examiner Name	Fetsum Abraham
Sheet	4	of	12	Attorney Docket Number	0756-7218

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				Examiner Name	Fetsum Abraham	
Sheet	8	of .	12	Attorney Docket Number	0756-7218	

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Examiner Initials	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), data, page(s), volume-issue number(s), publisher, city and/or country where published.								
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Application Number 10/712,062
Filling Date November 14, 2003
First Named Inventor Shunpei YAMAZAKI et al.

(use as many sheets as necessary) 2826 **Group Art Unit** EA 2 7 2008 Fetsum Abraham **Examiner Name** of **Attorney Docket Number** 0756-7218 CUEUN **U.S. PATENT DOCUMENTS** U.S. Patent Document Date of Publication of Cited Pages, Columns, Lines, Where Examiner Document MM-DD-YYYY Relevant Passages or Relevant Figures Appear Name of Patentee or Applicant of Cited Document Kind Code² Number (if known) FOREIGN PATENT DOCUMENTS Cite Date of Publication of Cited Pages, Columns, Lines, Where Relevant Passages Examiner Foreign Patent Document Name of Patentee or Document MM-DD-YYYY Initials Applicant of Cited Document ۲¢ Kind Code¹ or Relevant Figures Appear Number⁴ Office³ (if known) OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS T² Examiner Cite Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the Initials item (book, magazine, journal, serial, symposium, catalog, etc.)., date, page(s), volume-issue number(s), publisher, city and/or country where published. Office Action dated August 3, 1998 for Application Serial No. 08/784,293. Office Action dated February 11, 1999 for Application No. 08/784,293. Office Action dated January 17, 2003 for Application No. 08/784,293. Examiner

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Complete if Known Substitute for form 1449A/PTO 10/712,062 **Application Number INFORMATION DISCLOSURE** November 14, 2003 Filing Date STATEMENT BY APPLICANT Shunpei YAMAZAKI et al. First Named Inventor (use as many sheets as necessary) 2826 **Group Art Unit** F. Abraham **Examiner Name** Sheet **Attorney Docket Number** of 0756-7218

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